

# **Excellent Integrated System Limited**

Stocking Distributor

Click to view price, real time Inventory, Delivery & Lifecycle Information:

<u>Vishay Semiconductor/Diodes Division</u> <u>V80100PW-M3/4W</u>

For any questions, you can email us directly: <a href="mailto:sales@integrated-circuit.com">sales@integrated-circuit.com</a>

### Distributor of Vishay Semiconductor/Diodes Division: Excellent Integrated System Limite Datasheet of V80100PW-M3/4W - DIODE ARRAY SCHOTTKY 100V TO3PW

Contact us: sales@integrated-circuit.com Website: www.integrated-circuit.com



### V80100PW

Vishay General Semiconductor

## **Dual High-Voltage Trench MOS Barrier Schottky Rectifier**

Ultra Low  $V_F = 0.43 \text{ V}$  at  $I_F = 10 \text{ A}$ 



TMBS <sup>®</sup>
TO-3PW

#### **FEATURES**

- Trench MOS Schottky technology
- · Low forward voltage drop, low power losses

COMPLIANT

• High efficiency operation

• Solder dip 275 °C max. 10 s, per JESD 22-B106 FREE

• Material categorization: For definitions of compliance please see www.vishay.com/doc?99912

#### TYPICAL APPLICATIONS

For use in high frequency converters, switching power supplies, freewheeling diodes, OR-ing diode, DC/DC converters and reverse battery protection.

#### **MECHANICAL DATA**

Case: TO-3PW

Molding compound meets UL 94 V-0 flammability rating Base P/N-M3 - halogen-free, RoHS-compliant, and

commercial grade

Terminals: Matte tin plated leads, solderable per

J-STD-002 and JESD 22-B102

M3 suffix meets JESD 201 class 1A whisker test

Polarity: As marked

Mounting Torque: 10 in-lbs maximum

PRIMARY CHARACTERISTICS				
2 x 40 A				
100 V				
450 A				
700 mJ				
0.64 V				
150 °C				
TO-3PW				
Dual common cathode				

MAXIMUM RATINGS (T <sub>A</sub> = 25 °C unless otherwise noted)					
PARAMETER		SYMBOL	V80100PW	UNIT	
Maximum repetitive peak reverse voltage		$V_{RRM}$	100	V	
Maximum average forward rectified current (fig. 1)	per device	I <sub>F(AV)</sub>	80	- A	
	per diode		40		
Peak forward surge current 8.3 ms single half sine-wave superimposed on rated load per diode	I <sub>FSM</sub>	450	А		
Non-repetitive avalanche energy at T <sub>J</sub> = 25 °C, L = 180 r	E <sub>AS</sub>	700	mJ		
Peak repetitive reverse current at $t_p$ = 2 $\mu$ s, 1 kHz, $T_J$ = 38 °C $\pm$ 2 °C per diode	I <sub>RRM</sub>	1.0	А		
Voltage rate of change (rated V <sub>R</sub> )	dV/dt	10 000	V/µs		
Operating junction and storage temperature range	$T_J$ , $T_{STG}$	-40 to +150	°C		

# Distributor of Vishay Semiconductor/Diodes Division: Excellent Integrated System Limite

Contact us: sales@integrated-circuit.com Website: www.integrated-circuit.com





www.vishay.com

## Vishay General Semiconductor

<b>ELECTRICAL CHARACTERISTICS</b> (T <sub>A</sub> = 25 °C unless otherwise noted)							
PARAMETER	TEST CONDITIONS		SYMBOL	TYP.	MAX.	UNIT	
Breakdown voltage	I <sub>R</sub> = 1.0 mA	T <sub>A</sub> = 25 °C	$V_{BR}$	100 (minimum)	-	V	
Instantaneous forward voltage per diode	I <sub>F</sub> = 10 A	T <sub>A</sub> = 25 °C		0.49	-		
	I <sub>F</sub> = 20 A			0.59	-		
	I <sub>F</sub> = 40 A		V <sub>E</sub> (1)	0.76	0.84	V	
	I <sub>F</sub> = 10 A	T <sub>J</sub> = 125 °C	'	V <sub>F</sub> (··)	0.43	-	V
	I <sub>F</sub> = 20 A				0.55	-	
	I <sub>F</sub> = 40 A			0.64	0.76		
Reverse current per diode	V <sub>R</sub> = 80 V	T <sub>A</sub> = 25 °C	· I <sub>R</sub> <sup>(2)</sup>	38	-	μΑ	
	v <sub>R</sub> = 00 v	T <sub>A</sub> = 125 °C		17	-	mA	
	V <sub>R</sub> = 100 V	T <sub>A</sub> = 25 °C		85	1000	μΑ	
	$V_{R} = 100 V$ $T_{A} = 12$	T <sub>A</sub> = 125 °C		33	76	mA	

#### Notes

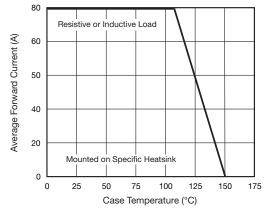
(1) Pulse test: 300 µs pulse width, 1 % duty cycle

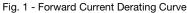
(2) Pulse test: Pulse width  $\leq$  40 ms

THERMAL CHARACTERISTICS (T <sub>A</sub> = 25 °C unless otherwise noted)						
PARAMETER		SYMBOL	V80100PW	UNIT		
Typical thermal resistance	per diode	$R_{ heta JC}$	1.5	°C/W		
	per device		0.8			

ORDERING INFORMATION (Example)							
PACKAGE	PREFERRED P/N	UNIT WEIGHT (g)	PACKAGE CODE	BASE QUANTITY	DELIVERY MODE		
TO-3PW	V80100PW-M3/4W	4.5	4W	30/tube	Tube		

### RATINGS AND CHARACTERISTICS CURVES (T<sub>A</sub> = 25 °C unless otherwise noted)





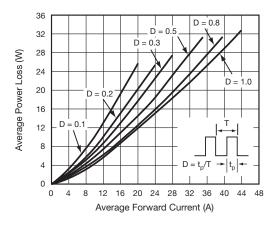


Fig. 2 - Forward Power Loss Characteristics Per Diode

Datasheet of V80100PW-M3/4W - DIODE ARRAY SCHOTTKY 100V TO3PW Contact us: sales@integrated-circuit.com Website: www.integrated-circuit.com



### www.vishay.com

### V80100PW

### Vishay General Semiconductor

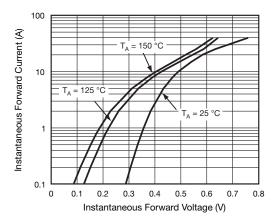


Fig. 3 - Typical Instantaneous Forward Characteristics Per Diode

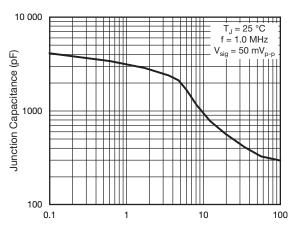


Fig. 5 - Typical Junction Capacitance Per Diode

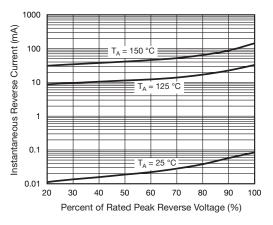


Fig. 4 - Typical Reverse Characteristics Per Diode

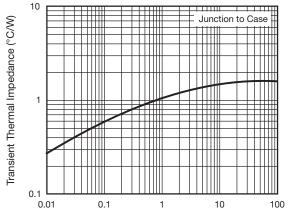
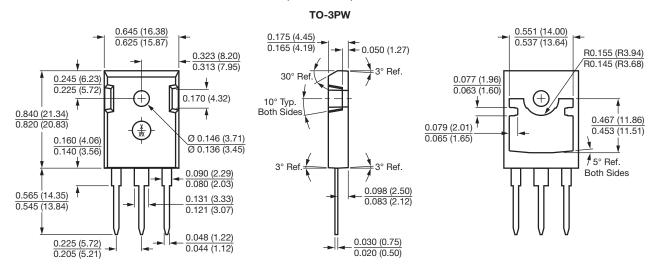


Fig. 6 - Typical Transient Thermal Impedance Per Diode

#### **PACKAGE OUTLINE DIMENSIONS** in inches (millimeters)



Revision: 20-Dec-13 3 Document Number: 89183



# Distributor of Vishay Semiconductor/Diodes Division: Excellent Integrated System Limite Datasheet of V80100PW-M3/4W - DIODE ARRAY SCHOTTKY 100V TO3PW

Contact us: sales@integrated-circuit.com Website: www.integrated-circuit.com



VISHAY. \_

www.vishay.com

Vishay

### **Disclaimer**

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.

Revision: 13-Jun-16 1 Document Number: 91000